

## P-Channel 30V (D-S) MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> ( $\Omega$ )	I <sub>D</sub> (A) <sup>d</sup>
- 30	0.018 at V <sub>GS</sub> = - 10 V	- 13
	0.030 at V <sub>GS</sub> = - 4.5 V	- 10

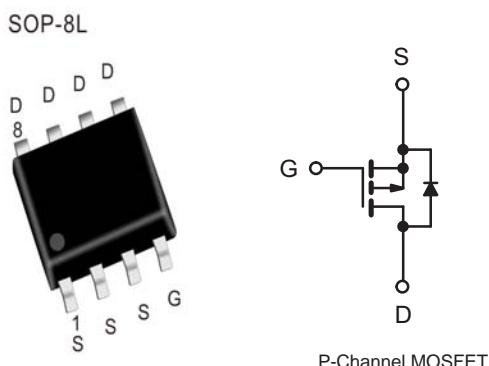
### Features

- Low Gate Charge
- RoHS Compliant

### Applications

- Load Switches
  - Notebook PCs
  - Desktop PCs

### Pin Configuration



### Packing Information

Device	Marking	Reel Size	Tape Width	Quantity
ECG4835	13D XXX	12"	13mm	3000pcs

### Absolute Maximum Ratings (T<sub>J</sub>=25 °C Unless Otherwise Noted)

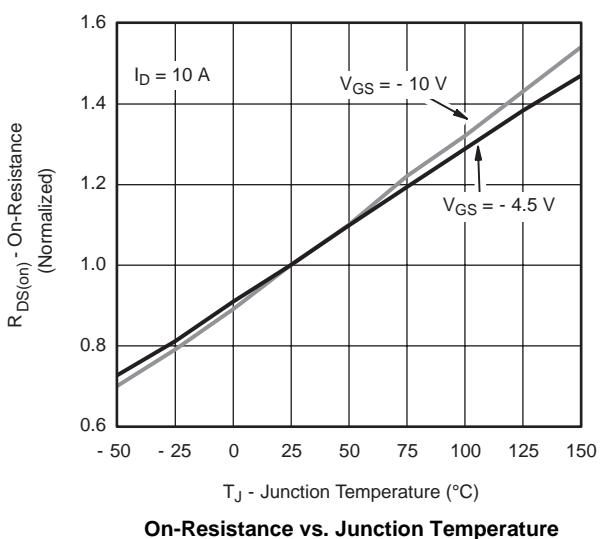
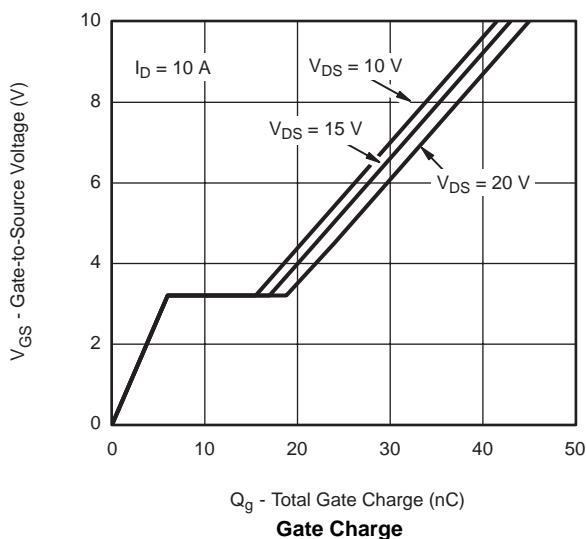
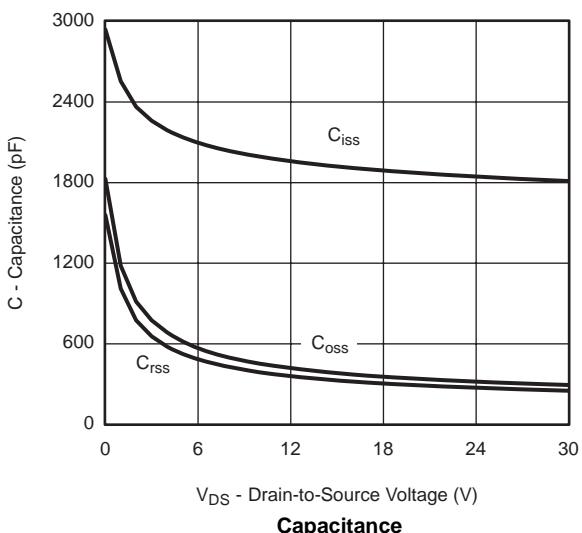
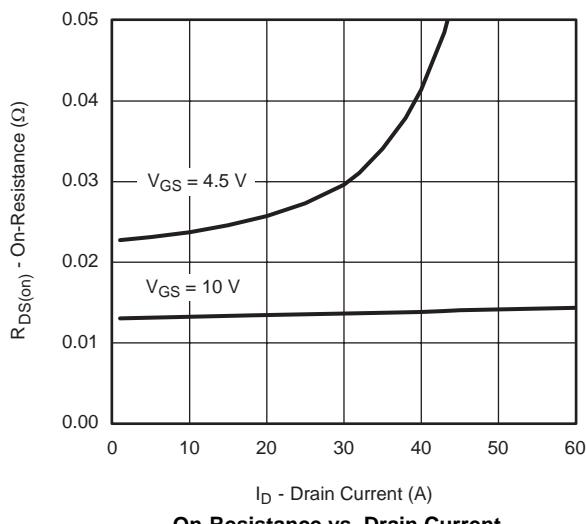
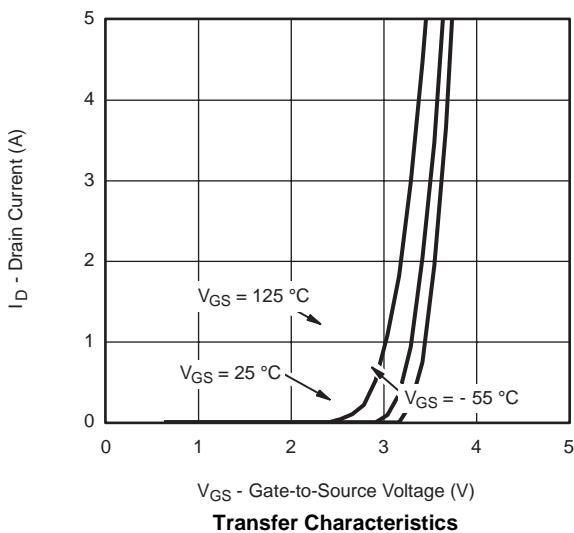
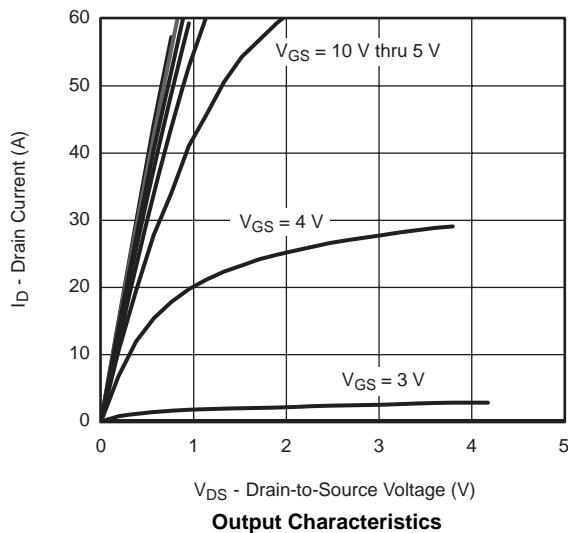
Symbol	Parameter	Value	Unit
<b>P-MOSFET</b>			
V <sub>DS</sub>	Drain-Source Voltage	-30	V
V <sub>GS</sub>	Gate-Source Voltage	$\pm 25$	V
I <sub>D</sub>	Continuous Drain Current	-13	A
I <sub>DM</sub>	Pulse Drain Current	-50	A
P <sub>D</sub>	Maximum Power Dissipation	5.6	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C
T <sub>L</sub>	Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	260	°C
<b>Thermal Resistance Ratings</b>			
R <sub>thJA</sub>	Maximum Junction-to-Ambient t≤10 s	50	°C/W
R <sub>thJF</sub>	Maximum Junction-to-Foot (Drain) Steady State	22	°C/W

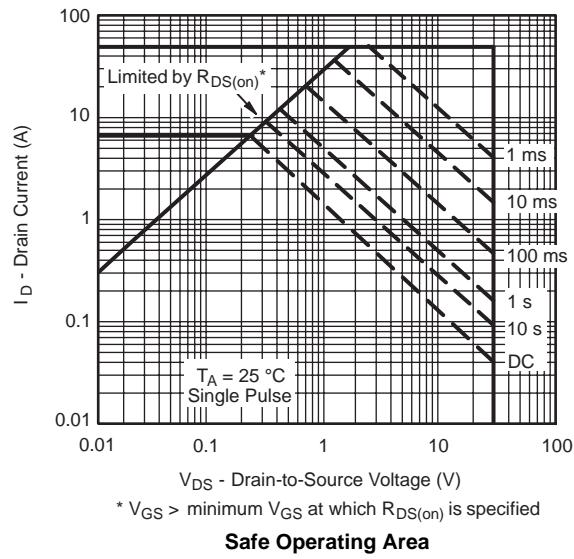
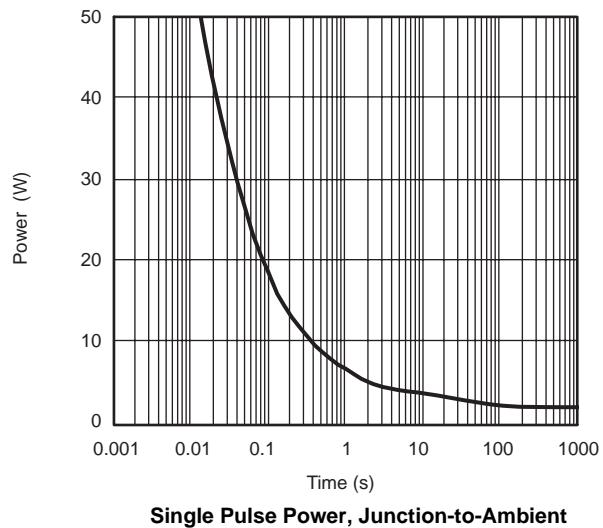
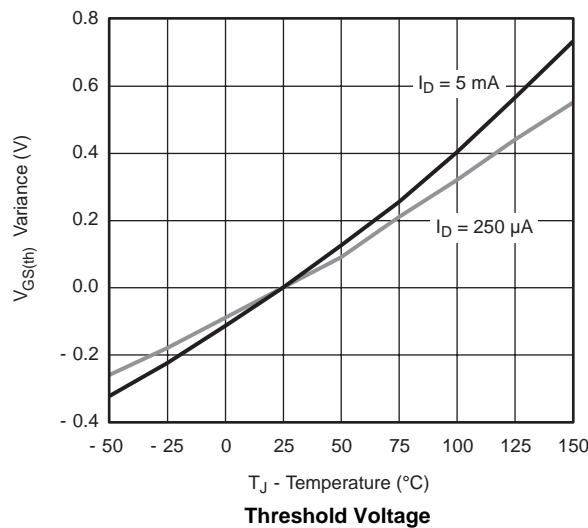
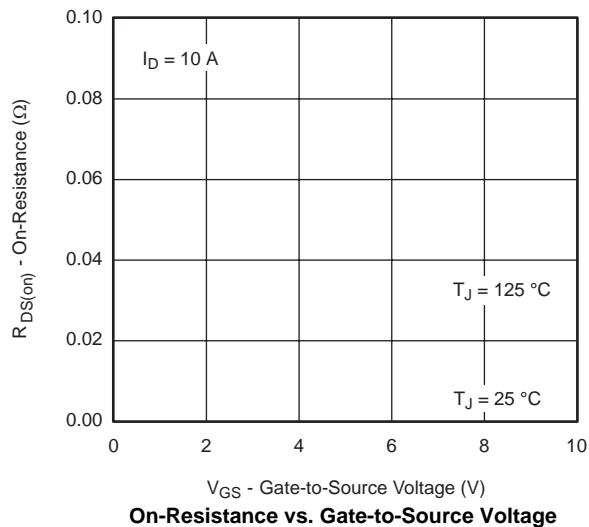
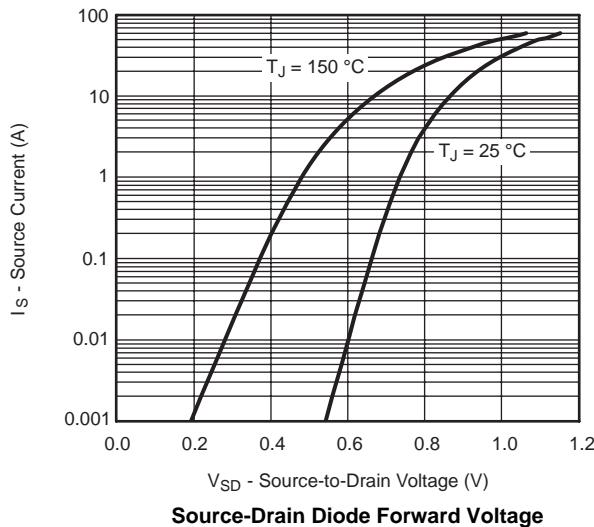
Notes:

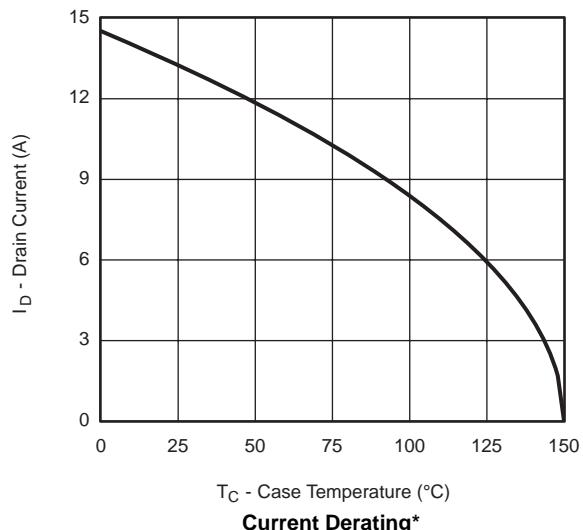
- a. Surface mounted on 1" x 1" FR4 board.
- b. t = 10 s.
- c. Maximum under Steady State conditions is 85 °C/W.
- d. Based on T<sub>C</sub> = 25 °C.

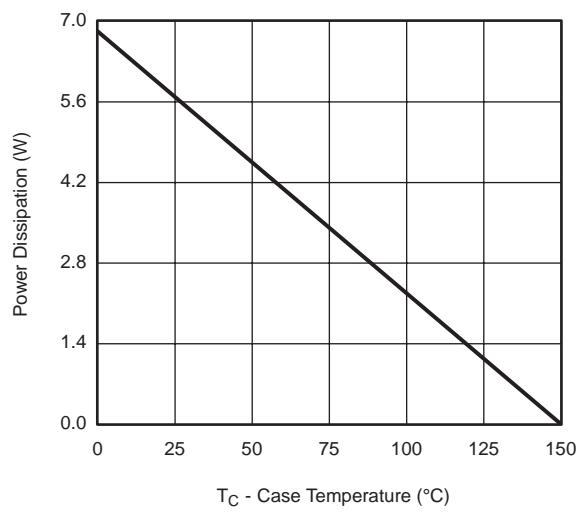
**Electrical Characteristics (T<sub>J</sub>=25°C Unless Otherwise Specified)**

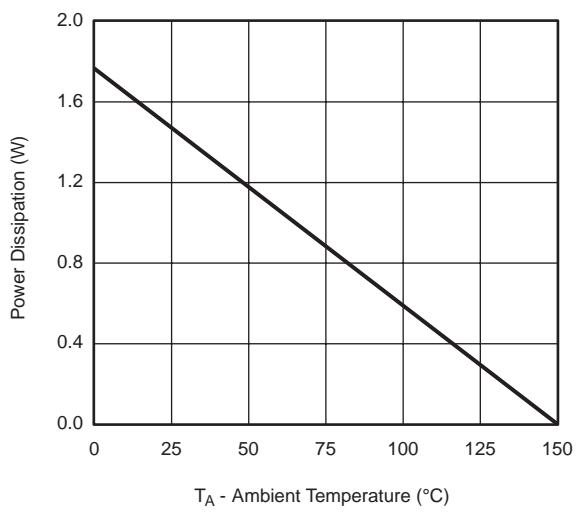
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
<b>STATIC PARAMETERS</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = - 250 μA	- 30			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V			-1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±25V, V <sub>DS</sub> = 0V			±100	nA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	-1.0		-3.0	V
Drain-source on-resistance(note1)	R <sub>D(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -10A		14	18	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -7A		24.5	30	mΩ
Forward transconductance(note1)	g <sub>FS</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -10A		23		S
Diode forward voltage(note1)	V <sub>SD</sub>	I <sub>S</sub> = -2A, V <sub>GS</sub> = 0V		-0.75	-1.2	V
<b>DYNAMIC</b>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz		1960		pF
Output capacitance	C <sub>oss</sub>			380		pF
Reverse transfer capacitance	C <sub>rss</sub>			325		pF
<b>SWITCHING PARAMETERS (note 2)</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS</sub> = -10V, V <sub>DD</sub> = -15V, R <sub>L</sub> = 3Ω, R <sub>G</sub> = 1Ω, I <sub>D</sub> = -5A		11	22	ns
Turn-on rise time	t <sub>r</sub>			13	25	ns
Turn-off delay time	t <sub>d(off)</sub>			32	50	ns
Turn-off fall time	t <sub>f</sub>			9	18	ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -10A		22	33	nC
Gate-Source Charge	Q <sub>gs</sub>			6		nC
Gate-Drain Charge	Q <sub>gd</sub>			11		nC

**MOSFET TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)**


**MOSFET TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)**


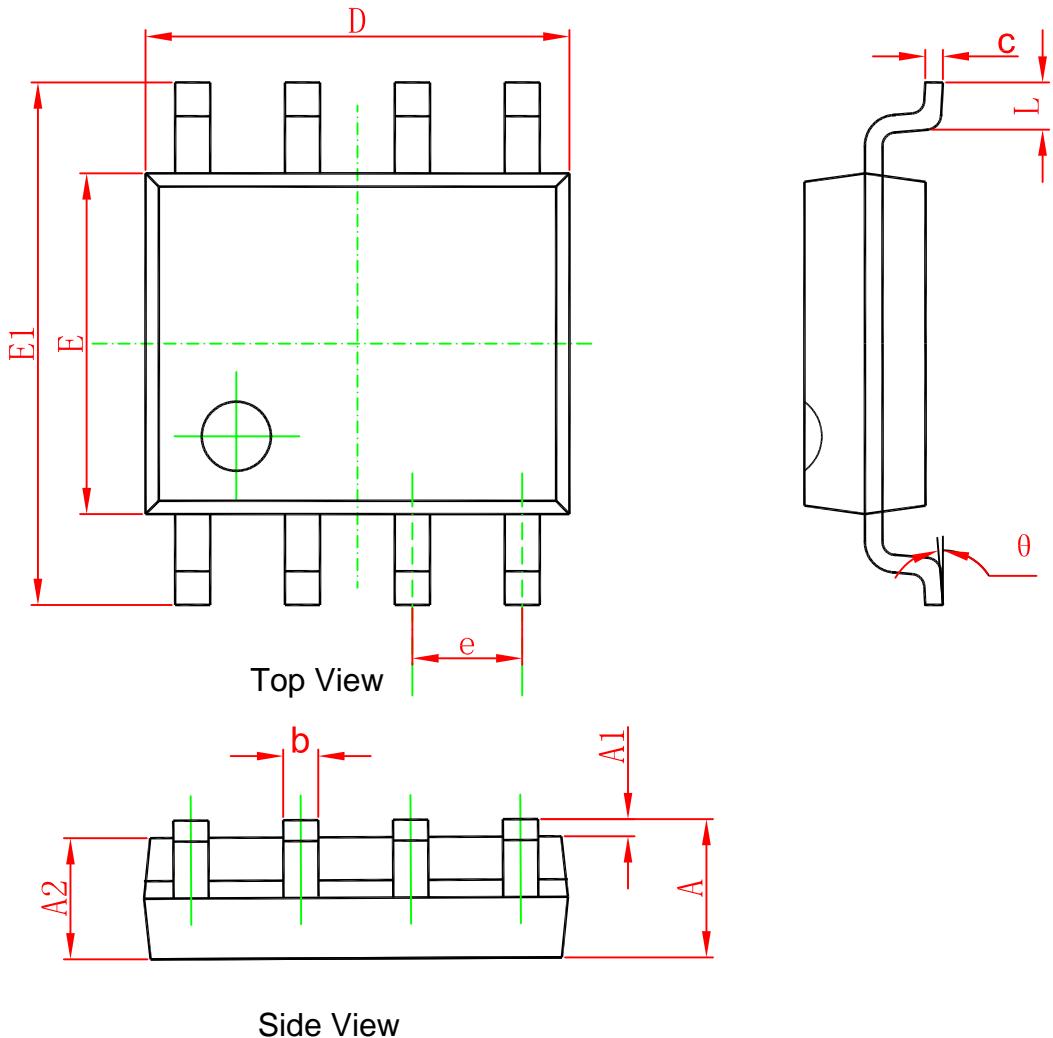
**MOSFET TYPICAL CHARACTERISTICS (25°C, unless otherwise noted)**

 $T_C$  - Case Temperature (°C)

**Current Derating\***

 $T_C$  - Case Temperature (°C)

**Power, Junction-to-Foot**

 $T_A$  - Ambient Temperature (°C)

**Power Derating, Junction-to-Ambient**

## SOP-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
$\theta$	0°	8°	0°	8°